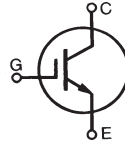


**GenX3™ 1200V IGBT**
**IXGA20N120B3  
IXGP20N120B3**

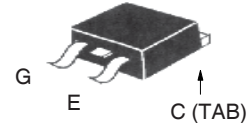
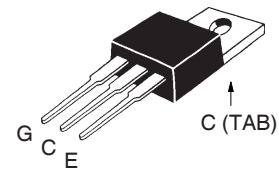
$$V_{CES} = 1200V$$

$$I_{C90} = 20A$$

$$V_{CE(sat)} \leq 3.1V$$

 High Speed Low Vsat PT  
IGBTs 3-20 kHz Switching


Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	1200	V
$V_{CGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ , $R_{GE} = 1M\Omega$	1200	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ\text{C}$	36	A
$I_{C90}$	$T_C = 90^\circ\text{C}$	20	A
$I_{CM}$	$T_C = 25^\circ\text{C}$ , 1ms	80	A
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15V$ , $T_J = 125^\circ\text{C}$ , $R_G = 15\Omega$ Clamped Inductive load	$I_{CM} = 40$ @ $V_{CE} \leq 1200$	A V
$P_C$	$T_C = 25^\circ\text{C}$	180	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$M_d$	Mounting Torque (TO-220)	1.13/10	Nm/lb.in.
$F_C$	Mounting Force (TO-263)	10..65 / 2.2..14.6	N/lb.
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
$T_{SOLD}$	1.6mm (0.062 in.) from Case for 10s	260	$^\circ\text{C}$
<b>Weight</b>	TO-263	2.5	g
	TO-220	3.0	g

**TO-263 (IXGA)**

**TO-220 (IXGP)**


G = Gate      C = Collector  
E = Emitter    TAB = Collector

**Features**

- Optimized for Low Conduction and Switching Losses
- Square RBSOA
- International Standard Packages

**Advantages**

- High Power Density
- Low Gate Drive Requirement

**Applications**

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Welding Machines
- Inductive Heating

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 250\mu\text{A}$ , $V_{GE} = 0V$	1200		V
$V_{GE(th)}$	$I_C = 250\mu\text{A}$ , $V_{CE} = V_{GE}$	2.5		V
$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$ $T_J = 125^\circ\text{C}$			25 $\mu\text{A}$ 1 mA
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 100$ nA
$V_{CE(sat)}$	$I_C = 16A$ , $V_{GE} = 15V$ , Note 2 $T_J = 125^\circ\text{C}$		2.7 2.8	3.1 V V

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$I_C = 16\text{A}, V_{CE} = 10\text{V}$ , Note 2	7.5	12.5	S
$C_{ies}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		1070	pF
$C_{oes}$			80	pF
$C_{res}$			32	pF
$Q_g$	$I_C = 16\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		51	nC
$Q_{ge}$			7.4	nC
$Q_{gc}$			23	nC
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = 16\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 600\text{V}, R_G = 15\Omega$ Note 1		16	ns
$t_{ri}$			31	ns
$E_{on}$			0.92	mJ
$t_{d(off)}$			150	ns
$t_{fi}$			155	ns
$E_{off}$			0.56	mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 125^\circ\text{C}</math></b> $I_C = 16\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 600\text{V}, R_G = 15\Omega$ Note 1		16	ns
$t_{ri}$			45	ns
$E_{on}$			1.60	mJ
$t_{d(off)}$			180	ns
$t_{fi}$			540	ns
$E_{off}$			1.63	mJ
$R_{thJC}$	TO-220			0.69 °C/W
$R_{thCK}$			0.50	°C/W

- Notes:
- Switching Times may Increase for  $V_{CE}$  (Clamp)  $> 0.5 \cdot V_{CES}$ , Higher  $T_J$  or Increased  $R_G$ .
  - Pulse Test,  $t \leq 300\mu\text{s}$ ; Duty Cycle,  $d \leq 2\%$ .

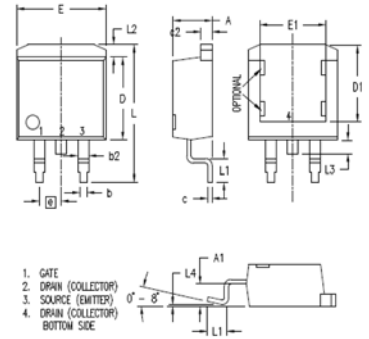
### PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

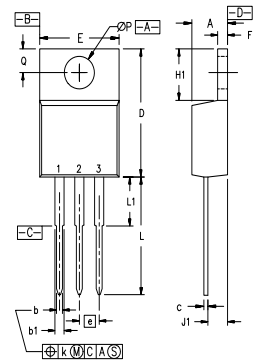
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

### TO-263 (IXGA) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

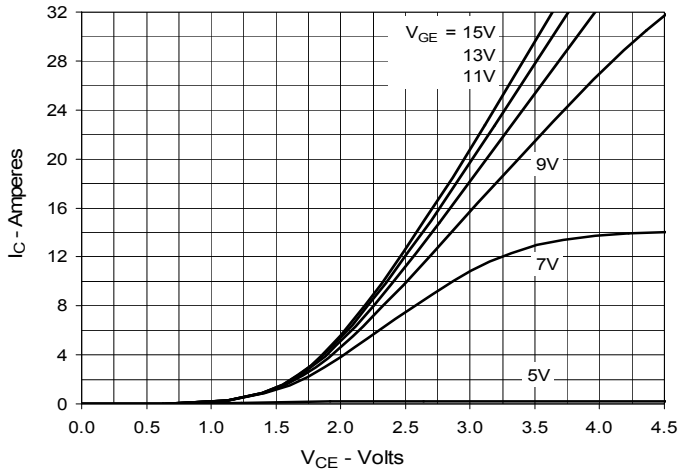
### TO-220 (IXGP) Outline



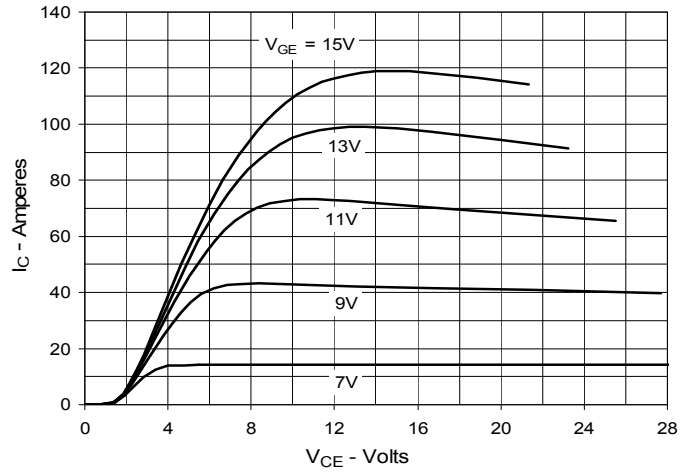
Pins: 1 - Gate 2 - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

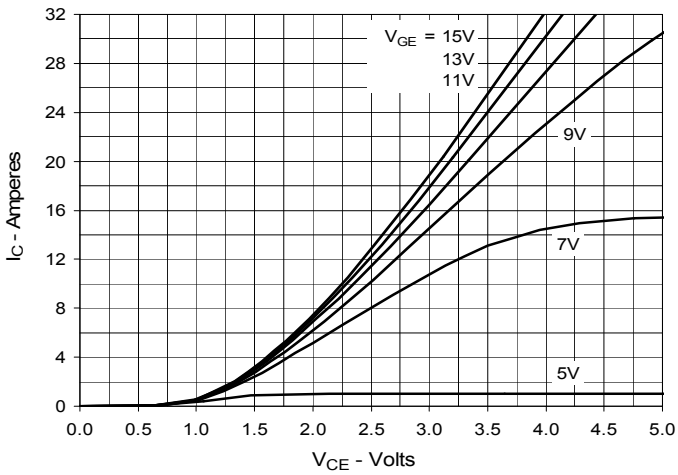
**Fig. 1. Output Characteristics @ 25°C**



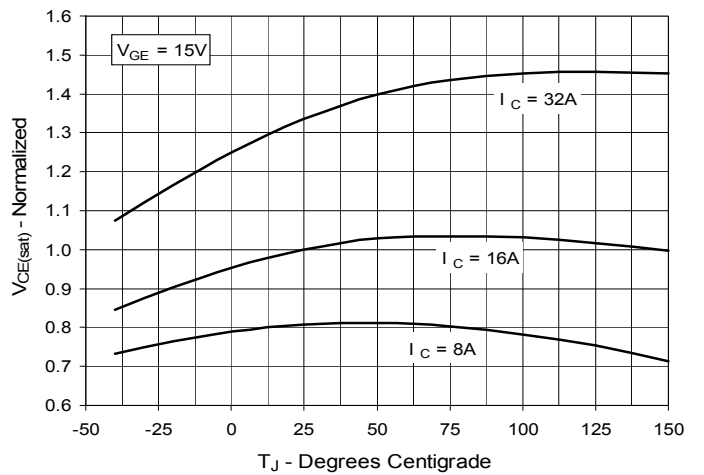
**Fig. 2. Extended Output Characteristics @ 25°C**



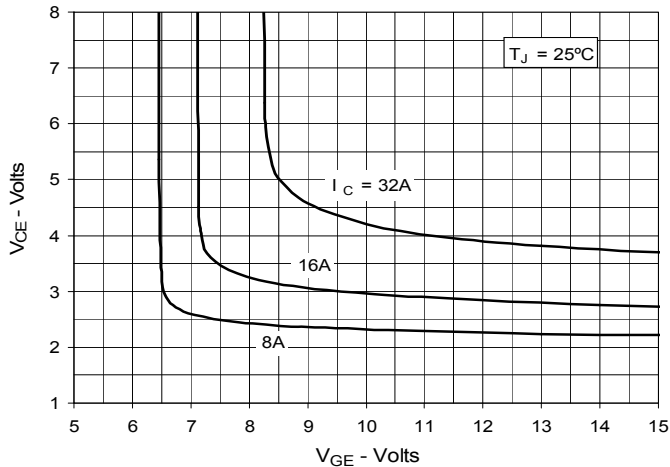
**Fig. 3. Output Characteristics @ 125°C**



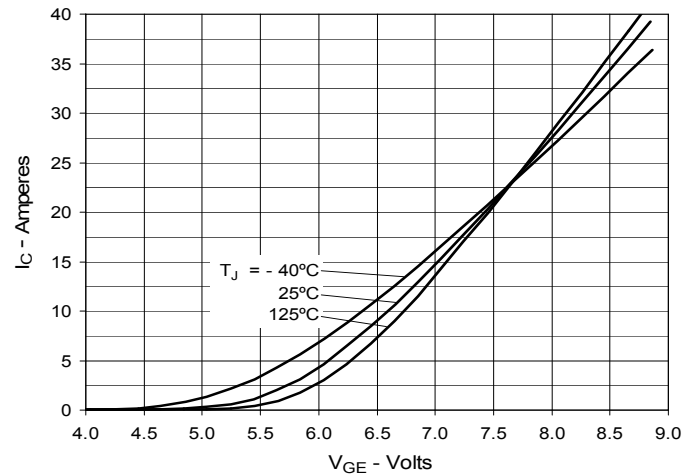
**Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature**



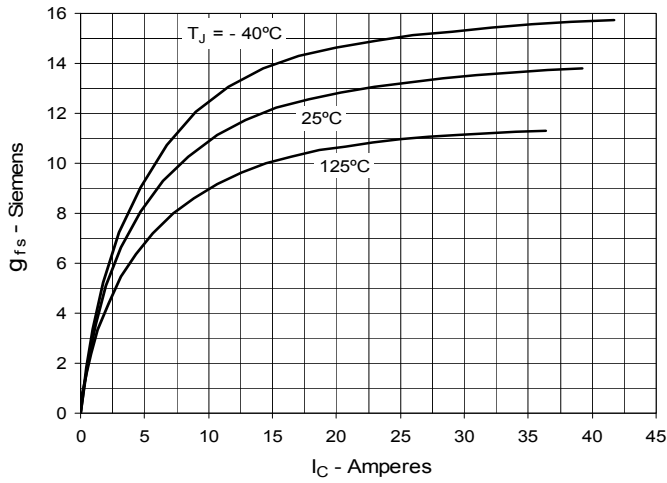
**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**



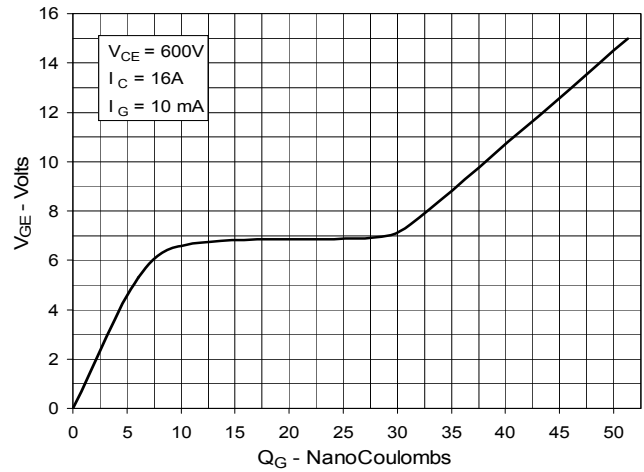
**Fig. 6. Input Admittance**



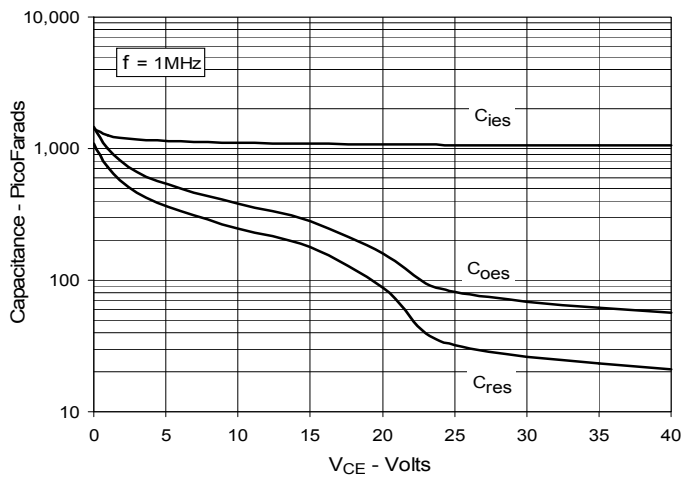
**Fig. 7. Transconductance**



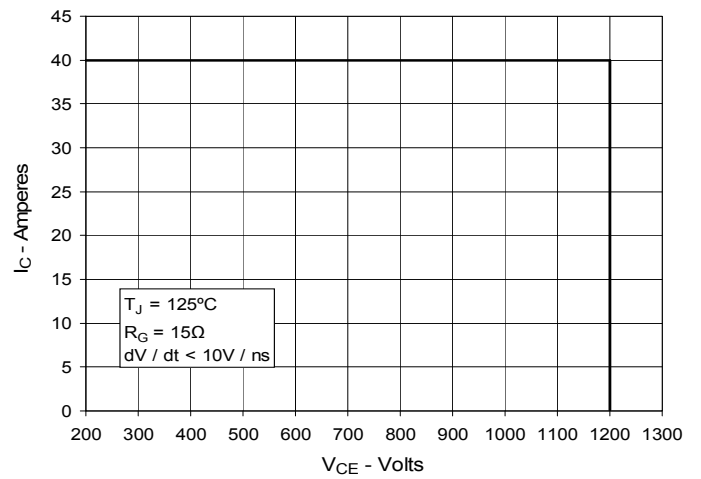
**Fig. 8. Gate Charge**



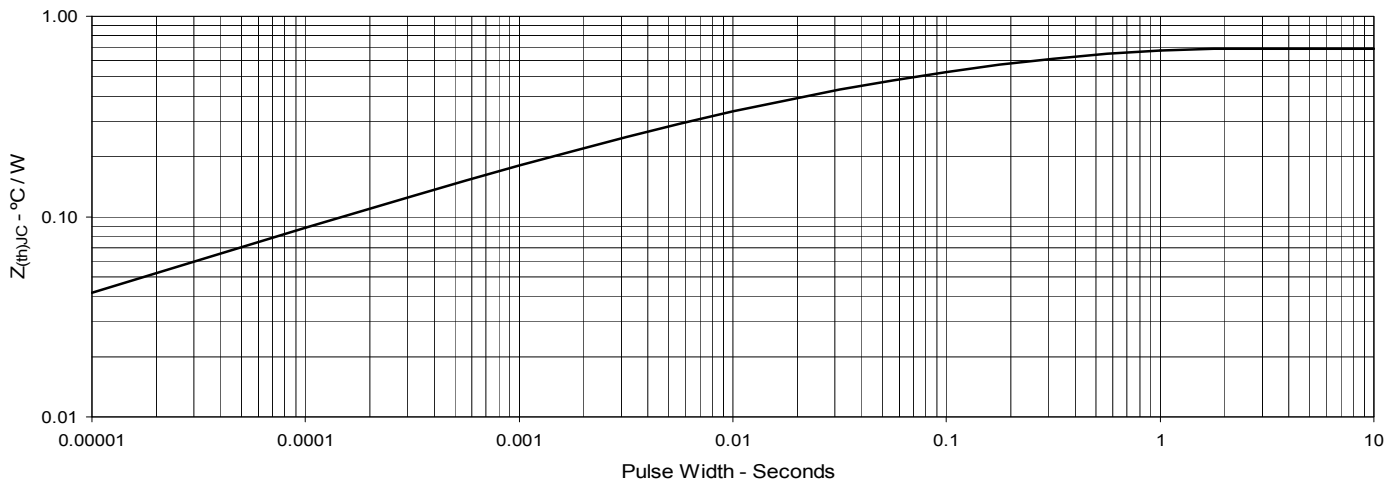
**Fig. 9. Capacitance**



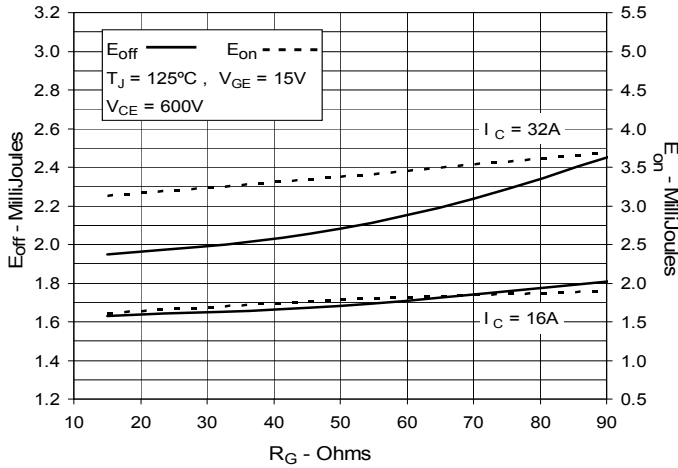
**Fig. 10. Reverse-Bias Safe Operating Area**



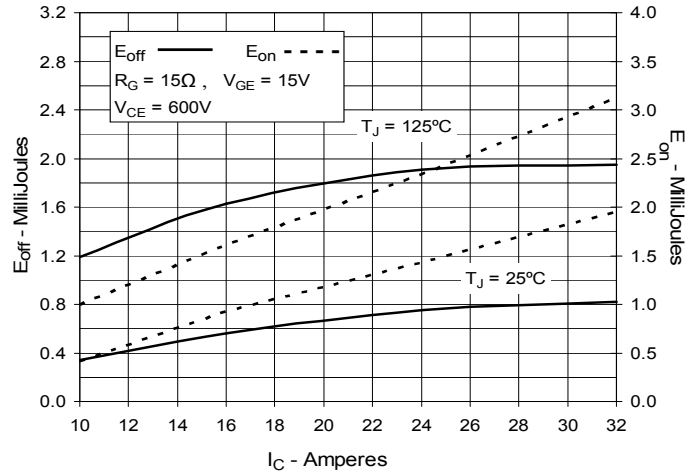
**Fig. 11. Maximum Transient Thermal Impedance**



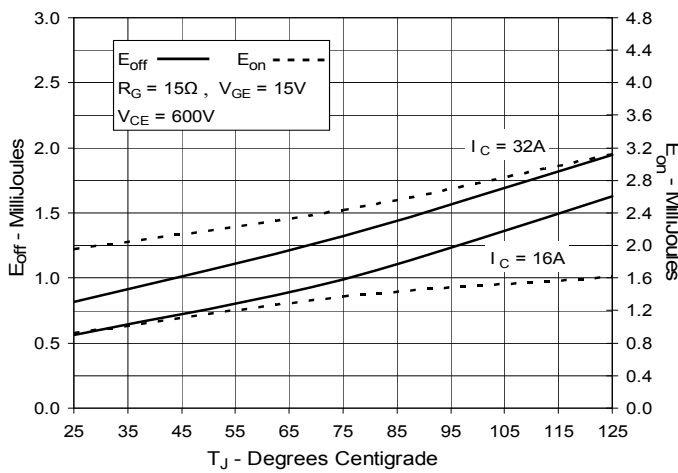
**Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance**



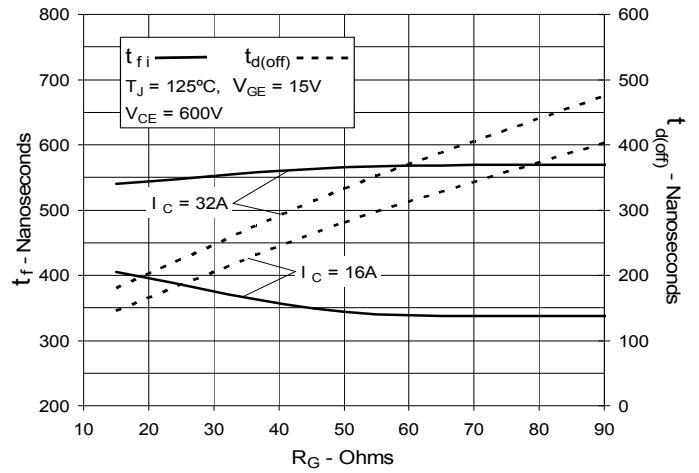
**Fig. 13. Inductive Switching Energy Loss vs. Collector Current**



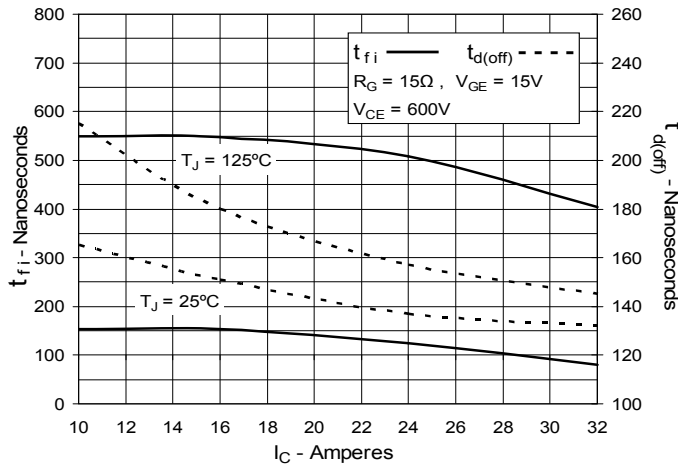
**Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature**



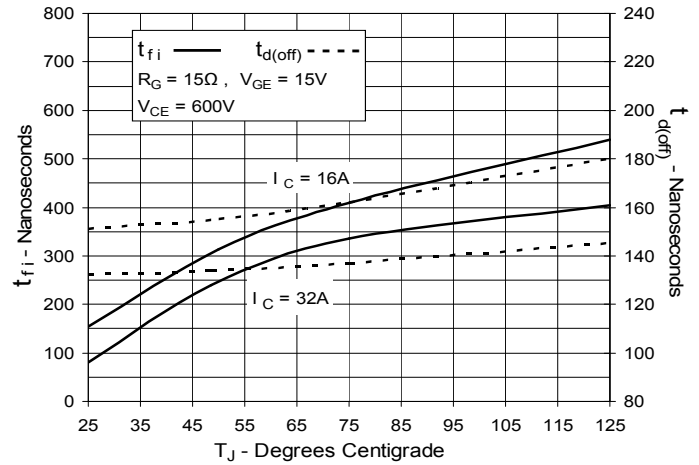
**Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance**



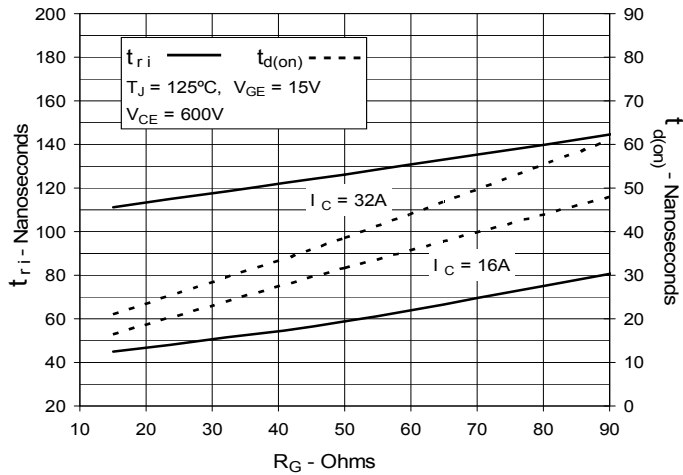
**Fig. 16. Inductive Turn-off Switching Times vs. Collector Current**



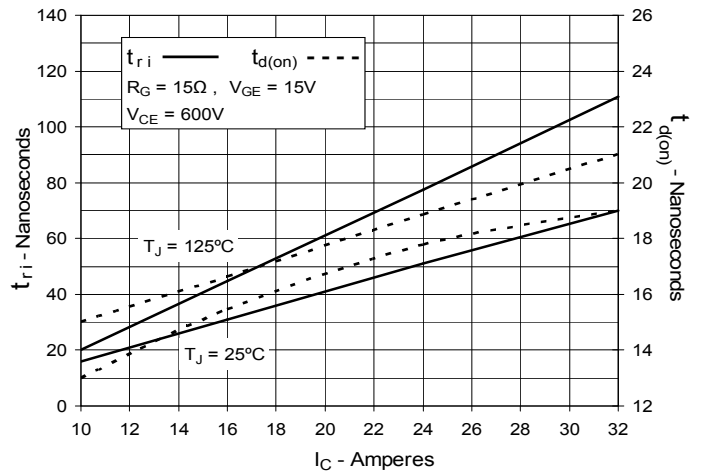
**Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature**



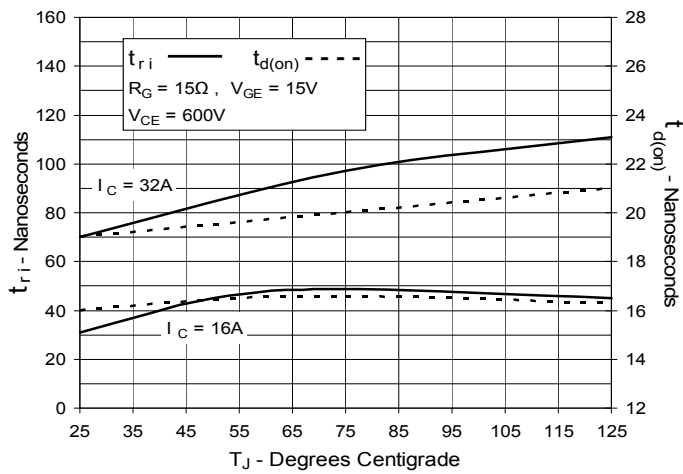
**Fig. 18. Inductive Turn-on  
Switching Times vs. Gate Resistance**



**Fig. 19. Inductive Turn-on  
Switching Times vs. Collector Current**



**Fig. 20. Inductive Turn-on  
Switching Times vs. Junction Temperature**





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